

9097250 TOSHIBA (DISCRETE/OPTO)

56C 07103

D T-29-25

10-98-7

T-03-09

FET

Type	Application	Electrical characteristic (Ta = 25°C)					Marking	Similar Type	Remarks
		V _{DSX} ** V _{GD0} V _{GRD} * (V)	I _{G, I_D} * (mA)	P _D (mW)	I _{SS} (mA)	Y _{fsl} (mS)			
2SK208	Low frequency amplifier	-50	10	100	0.3 ~ 6.5	1.2 MIN.	J	2SK30ATM	
2SK209	Low noise low frequency amplifier	-50	10	150	0.6 ~ 14	15	X	2SK117	
2SK210	FM RF amplifier	-18*	10	100	3.0 ~ 24	7 TYP.	Y	2SK192A	
2SK211	FM RF amplifier	-18*	10	100	1.0 ~ 10	9 TYP.	K	2SK161	
2SK302	VHF band amplifier	20**	30*	150	1.5 ~ 14	10 TYP.	T	2SK241	MOS type FET

Diode

Type	Application	Electrical Characteristic (Ta = 25°C)					Marking	Similar Type	
		V _R (V)	I _F (mA)	C _r (PE)	NF(dB)	R _s (Ω)			
ISS154	UHF ~ S band mixer detector	6	30	0.8	9 MAX.	-	BA	-	
ISV128	VHF ~ UHF band attenuator	50	50	0.25	-	7	BB	ISV99	
ISS181	High Speed Switching	80	100	4.0	-	-	A3	-	Cathode Common
ISS184	High Speed Switching	80	100	4.0	-	-	B3	-	Anode Common
ISS226	High Speed Switching	80	100	4.0	-	-	C3	-	Series Type

TOSHIBA CORPORATION